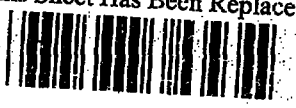
This Sheet Has Been Replaced



ABSTRACT OF THE DISCLOSURE

TITLE OF INVENTION: SEMICONDUCTOR STORAGE DEVICE AND METHOD OF DRIVING THE SAME

A drain region and a source region are formed in a silicon substrate, and a select gate is formed on the substrate between the source and drain regions with a gate insulating film sandwiched. On one side of the select gate, a floating-gate is formed out of a sidewall formed with an insulating film sandwiched. On the floating-gate and the select gate, a control gate is formed with an insulating film sandwiched. The insulating film directly below the floating-gate is formed as a tunnel oxide film which can allow FN tunneling of electrons. In an erase operation, electrons are injected into the floating-gate from the silicon substrate, and in a write operation, electrons are extracted from the floating-gate to the drain region. A current required for writing and erasing each cell can be decreased, a low power supply can be used, and the lifetime of the tunnel insulating film can be elongated. Thus, the invention provides a semiconductor storage device (EEPROM) which works as a nonvolatile memory capable of page erase and page write at a low supply voltage.